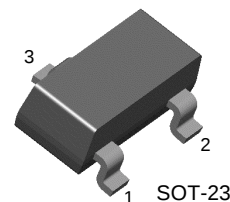


FJV992

Audio Frequency Low Noise Amplifier

- Complement to FJV1845



1. Base 2. Emitter 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_a=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-50	mA
P_C	Collector Power Dissipation	300	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-55 ~ 150	$^{\circ}\text{C}$

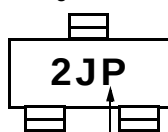
Electrical Characteristics $T_a=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = -100\mu\text{A}, I_E = 0$	-120		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}, I_B = 0$	-120		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}, I_C = 0$	-5		V
I_{EBO}	Emitter-Base Cutoff Current	$V_{EB} = -6\text{V}, I_C = 0$		-30	nA
h_{FE1} h_{FE2}	DC Current Gain	$V_{CE} = -6\text{V}, I_C = -0.1\text{mA}$ $V_{CE} = -6\text{V}, I_C = -1\text{mA}$	150 200	800	
$V_{CE}(\text{sat})$	Collector-Emitter Saturation Voltage	$I_C = -10\text{mA}, I_B = -1\text{mA}$		-300	mV
$V_{BE}(\text{on})$	Base-Emitter On Voltage	$V_{CE} = -6\text{V}, I_C = -1\text{mA}$	-0.55	-0.65	V
f_T	Current Gain Bandwidth Product	$V_{CE} = -6\text{V}, I_C = -1\text{mA}$	50		MHz
C_{ob}	Output Capacitance	$V_{CB} = -30\text{V}, I_E = 0, f = 1\text{MHz}$		3	pF
NV	Noise Voltage	$V_{CE} = -5.0\text{V}, I_C = -1.0\text{mA},$ $R_G = 100\text{KW}, G_V = 80\text{dB},$ $f = 10\text{Hz to } 1.0\text{KHz}$		40	mV

h_{FE2} Classification

Classification	P	F	E
h_{FE2}	200 ~ 400	300 ~ 600	400 ~ 800

Marking



h_{FE} Classification

Typical Characteristics

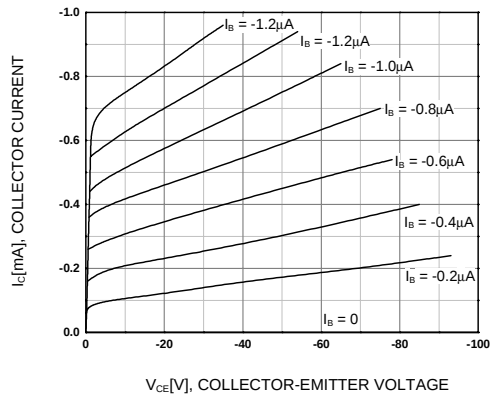


Figure 1. Static Characteristic

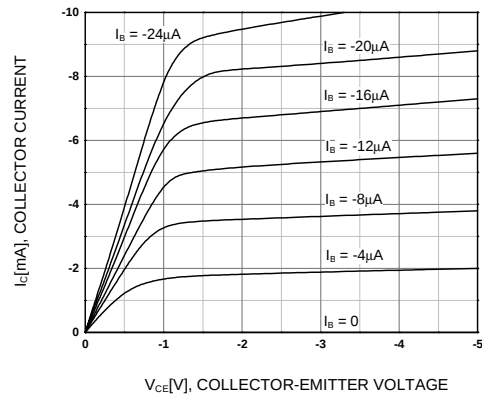


Figure 2. Static Characteristic

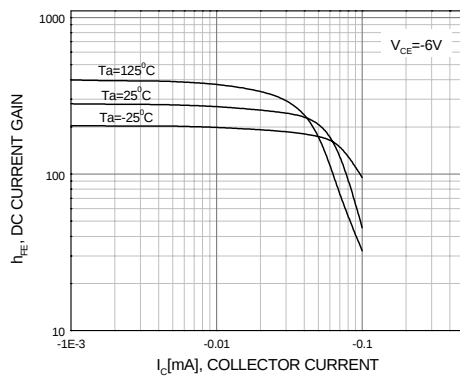


Figure 3. DC current Gain

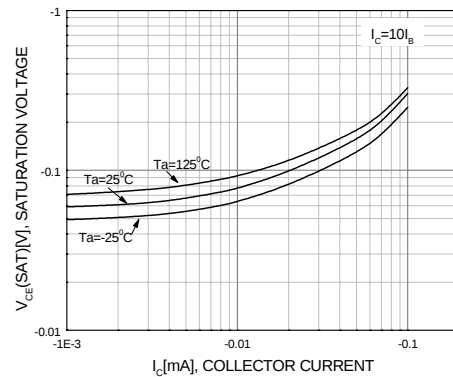


Figure 4. Collector-Emitter Saturation Voltage

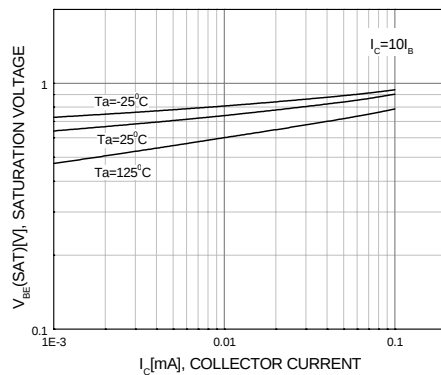


Figure 5. Base-Emitter Saturation Voltage

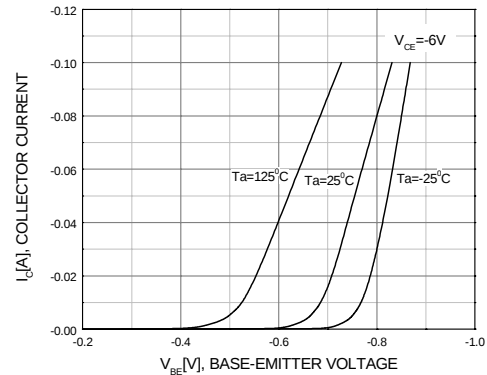


Figure 6. Base-Emitter Voltage

Typical Characteristics (Continued)

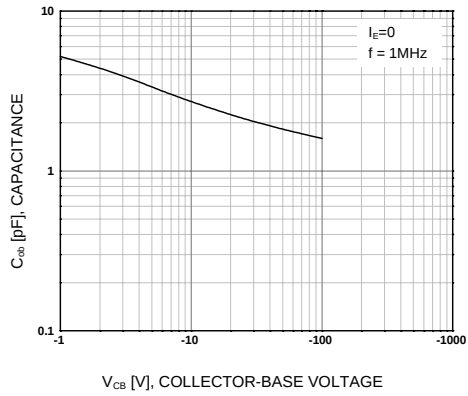


Figure 7. Collector Output Capacitance

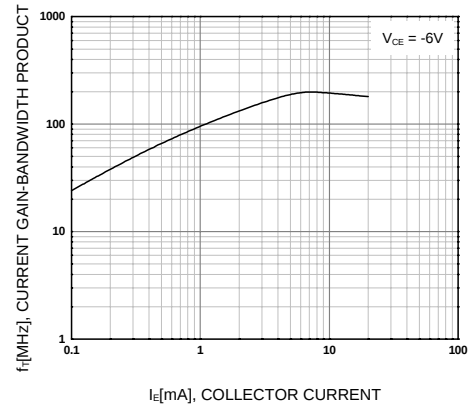


Figure 8. Current Gain Bandwidth Product

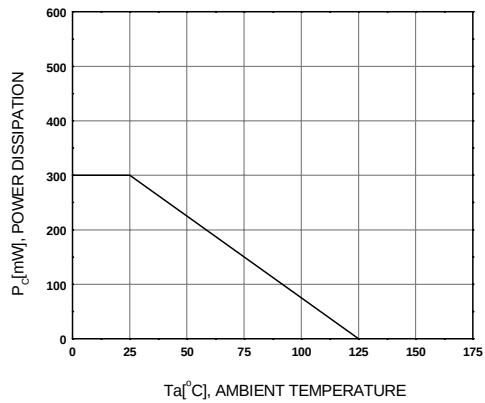
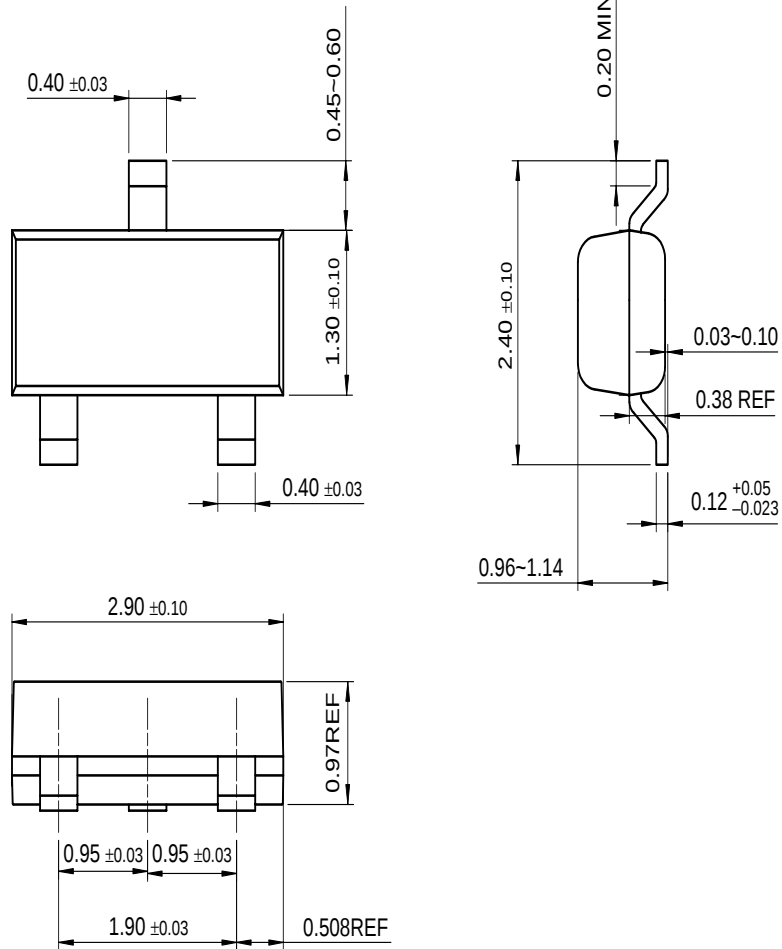


Figure 9. Power Derating

Package Dimensions

SOT-23



Dimensions in Millimeters

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